ABSTRACT OF THE DISCLOSURE

An exposure apparatus has an illuminating optical system for illuminating a mask with illuminating light from a light source, a projection optical system for projecting a pattern image, which has been formed on the mask, onto a wafer constituting a photosensitive substrate, and an alignment sensor constructing a position detection system for detecting an alignment mark on the wafer. The pattern region on the wafer is formed at a position offset toward the side of the alignment sensor from the projection center of the projection optical system, and the alignment sensor is disposed on the side near the pattern region formed on the wafer off-centered from the optic axis. By thus shortening baseline distance, the effects of measurement error due to baseline fluctuation can be reduced and it is possible to achieve highly precise detection of the position of an object to be detected (a position detection mark) and highly precise alignment.